Unit in mm

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2 S A 9 6 5

POWER AMPLIFIER APPLICATIONS. DRIVER STAGE AMPLIFIER APPLICATIONS.

Complementary to 2SC2235.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	-120	V
Collector-Emitter Voltage	v_{CEO}	-120	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	IC	-800	mA
Emitter Current	$I_{\mathbf{E}}$	800	mA
Collector Power Dissipation	PC	900	mW
Junction Temperature	T_{j}	150	°C
Storage Temperature Range	$T_{ m stg}$	-55~150	°C

5.1 MAX 1.0 MAX 0.8 MAX0.5 MIN 0.6 MAX 1.27 1.27 4.1 MAX **EMITTER** COLLECTOR BASE TO-92MOD

JEDEC EIAJ TOSHIBA 2-5J1A

120

LATE TOWN LAW TINES

Weight: 0.36g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CITADA CONFIDIONICA

Transition Frequency

Collector Output Capacitance

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	$V_{CB} = -120V, I_{E} = 0$	_	_	-100	nA
Emitter Cut-off Current	$I_{ m EBO}$	$V_{EB} = -5V, I_C = 0$	_	_	-100	nA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	$I_{\rm C} = -10 {\rm mA}, I_{\rm B} = 0$	-120	1	_	V
Emitter -Base Breakdown Voltage	V _{(BR)EBO}	$I_{\rm E} = -1$ mA, $I_{\rm C} = 0$	-5		_	V
DC Current Gain	hFE (Note)	$V_{CE} = -5V, I_{C} = -100 \text{mA}$	80	l	240	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	$I_{C} = -500 \text{mA}, I_{B} = -50 \text{mA}$			-1.0	V
Base-Emitter Voltage	$V_{ m BE}$	$V_{CE} = -5V, I_{C} = -500 \text{mA}$	_		-1.0	V

 $V_{CE} = -5V, I_{C} = -100 \text{mA}$

 $V_{CB} = -10V, I_E = 0, f = 1MHz$

WEST CONDITION

Note: hFE Classification $O: 80\sim160, Y: 120\sim240$

 f_{T}

 C_{ob}

40

MHz

рF

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